

SN74LVC2G02 双路双输入正或非门

1 特性

- 采用德州仪器 (TI) 的 NanoFree™ 封装
- 支持 5V V_{CC} 运行
- 输入电压高达 5.5V
- 电压为 3.3V 时, t_{pd} 最大值为 4.9ns
- 低功耗, I_{CC} 最大值为 10 μ A
- 电压为 3.3V 时, 输出驱动为 ± 24 mA
- 在 $V_{CC} = 3.3V$, $T_A = 25^\circ C$ 时, V_{OLP} (输出接地反弹) 典型值小于 0.8V
- 在 $V_{CC} = 3.3V$, $T_A = 25^\circ C$ 时, V_{OHV} (输出 V_{OH} 下冲) 典型值大于 2V
- I_{off} 支持局部断电模式运行
- 闩锁性能超过 100mA, 符合 JESD 78 II 类规范要求
- ESD 保护性能超过 JESD 22 规范要求
 - 2000V 人体放电模型 (A114-A)
 - 1000V 充电器件模型 (C101)

2 应用

- AV 接收器
- 音频接口盒: 便携式
- 蓝光播放器与家庭影院
- 嵌入式 PC
- MP3 播放器/录音机 (便携式音响)
- 个人数字助理 (PDA)
- 电源: 电信/服务器交流/直流电源: 单路控制器: 模拟式和数字式
- 固态硬盘 (SSD): 客户端和企业级
- 电视: LCD 电视/数字电视和高清电视 (HDTV)
- 平板电脑: 企业级
- 视频分析: 服务器
- 无线耳机、键盘和鼠标

3 说明

按照设计, 此双路双输入正或非门可在 1.65V 至 5.5V V_{CC} 电压下运行。

SN74LVC2G02 器件以正逻辑执行布尔函数 $Y = \overline{A + B}$ 或 $Y = \overline{A} \times \overline{B}$ 。

NanoFree™ 封装技术是 IC 封装概念的一项重大突破, 它将硅晶片用作封装。

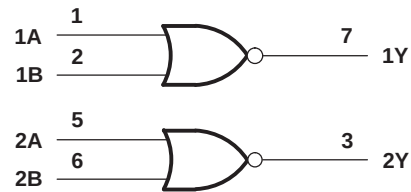
该器件完全适用于 I_{off} 为了部分断电的应用。 I_{off} 电路会禁用输出, 从而在器件掉电时防止电流回流损坏器件。

器件信息⁽¹⁾

器件号	封装	封装尺寸 (标称值)
SN74LVC2G02DCT	SSOP (8)	2.95mm × 2.8mm
SN74LVC2G02DCU	VSSOP (8)	2.3mm × 2.0mm
SN74LVC2G02YZP	DSBGA (8)	1.91mm × 0.91mm

(1) 如需了解所有可用封装, 请参阅数据表末尾的可订购产品附录。

简化原理图



目录

1	特性	1	8.1	Overview	9
2	应用	1	8.2	Functional Block Diagram	9
3	说明	1	8.3	Feature Description	9
4	修订历史记录	2	8.4	Device Functional Modes	9
5	Pin Configuration and Functions	3	9	Application and Implementation	10
6	Specifications	4	9.1	Application Information	10
6.1	Absolute Maximum Ratings	4	9.2	Typical Application	10
6.2	ESD Ratings	4	10	Power Supply Recommendations	11
6.3	Recommended Operating Conditions	5	11	Layout	11
6.4	Thermal Information	5	11.1	Layout Guidelines	11
6.5	Electrical Characteristics	6	11.2	Layout Example	11
6.6	Switching Characteristics	6	12	器件和文档支持	12
6.7	Switching Characteristics	6	12.1	社区资源	12
6.8	Operating Characteristics	6	12.2	商标	12
6.9	Typical Characteristics	7	12.3	静电放电警告	12
7	Parameter Measurement Information	8	12.4	Glossary	12
8	Detailed Description	9	13	机械、封装和可订购信息	12

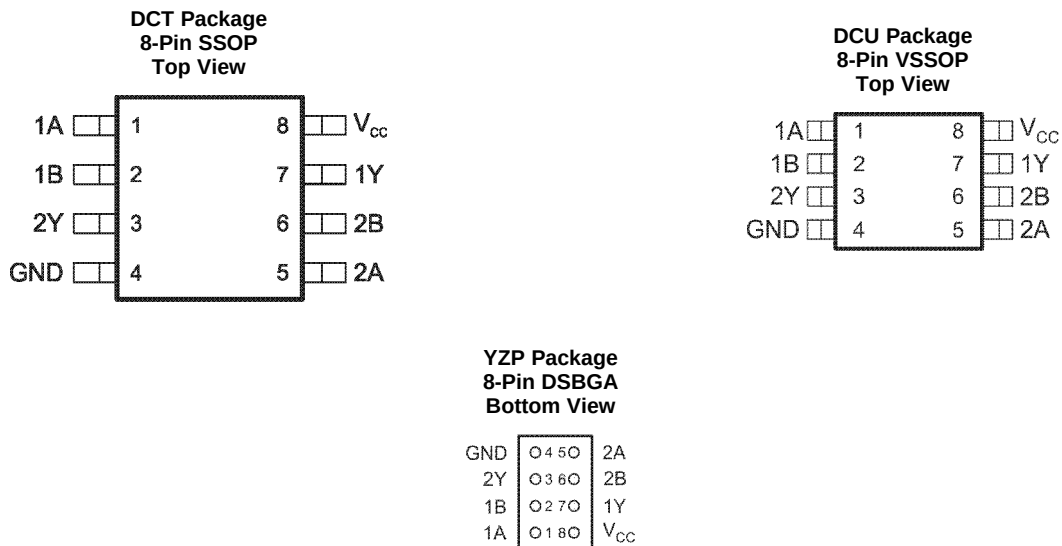
4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision M (November 2013) to Revision N	Page
• 将文档更新为新的 TI 数据表格式。	1
• 已添加 添加了器件信息表	1
• Added T _J (Max) spec to Abs Max Ratings table	4
• Moved T _{stg} spec to Abs Max Ratings table.	4

Changes from Revision L (April 1999) to Revision M	Page
• 删除了订购信息表。	1
• Updated operating temperature range.	5

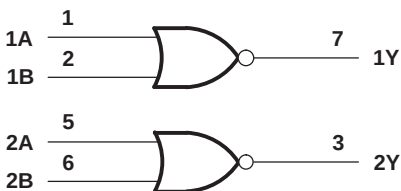
5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
1A	1	Input	Channel 1 input A
1B	2	Input	Channel 1 input B
2Y	3	Output	Channel 2 output Y
GND	4	–	Ground
2A	5	Input	Channel 2 input A
2B	6	Input	Channel 2 input B
1Y	7	Output	Channel 1 output Y
VCC	8	–	Positive supply

Logic Diagram (Positive Logic)



6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	6.5	V
V_I	Input voltage range ⁽²⁾		–0.5	6.5	V
V_O	Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾		–0.5	6.5	V
V_O	Voltage range applied to any output in the high or low state ⁽²⁾⁽³⁾		–0.5	$V_{CC} + 0.5$	V
I_{IK}	Input clamp current	$V_I < 0$		–50	mA
I_{OK}	Output clamp current	$V_O < 0$		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature		–65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (3) The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2500	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	Operating	1.65	5.5
		Data retention only	1.5	
V _{IH}	High-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	1.7	
		V _{CC} = 3 V to 3.6 V	2	
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}	
V _{IL}	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	0.7	
		V _{CC} = 3 V to 3.6 V	0.8	
		V _{CC} = 4.5 V to 5.5 V	0.3 × V _{CC}	
V _I	Input voltage	0	5.5	V
V _O	Output voltage	0	V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 1.65 V	–4	mA
		V _{CC} = 2.3 V	–8	
		V _{CC} = 3 V	–16	
		V _{CC} = 4.5 V	–24	
I _{OL}	Low-level output current	V _{CC} = 1.65 V	4	mA
		V _{CC} = 2.3 V	8	
		V _{CC} = 3 V	16	
		V _{CC} = 4.5 V	24	
Δt/Δv	Input transition rise or fall rate	V _{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V	20	ns/V
		V _{CC} = 3.3 V ± 0.3 V	10	
		V _{CC} = 5 V ± 0.5 V	5	
T _A	Operating free-air temperature	–40	125	°C

- (1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number [SCBA004](#).

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LVC2G02			UNIT
		DCT (SSOP)	DCU (VSSOP)	YZP (DSBGA)	
		8 PINS	8 PINS	8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	182.8	201.8	99.9	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	87.8	93.3	1.0	°C/W
R _{θJB}	Junction-to-board thermal resistance	97.9	124.0	27.8	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	20.7	32.3	0.4	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	96.6	123.6	27.8	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics application report](#).

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V _{CC}	–40°C to 85°C			–40°C to 125°C			UNIT
				MIN	TYP ⁽¹⁾	MAX	MIN	TYP ⁽¹⁾	MAX	
V _{OH}	I _{OH} = –100 μA		1.65 V to 5.5 V	V _{CC} – 0.1			V _{CC} – 0.1			V
	I _{OH} = –4 mA		1.65 V	1.2			1.2			
	I _{OH} = –8 mA		2.3 V	1.9			1.9			
	I _{OH} = –16 mA		3 V	2.4			2.4			
	I _{OH} = –24 mA			2.3			2.3			
	I _{OH} = –32 mA		4.5 V	3.8			3.8			
V _{OL}	I _{OL} = 100 μA		1.65 V to 5.5 V	0.1			0.1			V
	I _{OL} = 4 mA		1.65 V	0.45			0.45			
	I _{OL} = 8 mA		2.3 V	0.3			0.3			
	I _{OL} = 16 mA		3 V	0.4			0.4			
	I _{OL} = 24 mA			0.55			0.75			
	I _{OL} = 32 mA		4.5 V	0.55			0.75			
I _I	A or B inputs	V _I = 5.5 V or GND	0 to 5.5 V	±5			±5			μA
I _{off}	V _I or V _O = 5.5 V		0	±10			±10			μA
I _{CC}	V _I = 5.5 V or GND, I _O = 0		1.65 V to 5.5 V	10			10			μA
ΔI _{CC}	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND		3 V to 5.5 V	500			500			μA
C _I	V _I = V _{CC} or GND		3.3 V	5			5			pF

 (1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to 85°C								UNIT
			V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Y	3.2	8.9	1	5.4	1	4.9	1	4.4	ns

6.7 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to 125°C								UNIT
			V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Y	3.2	10.9	1	6.4	1	5.9	1	5.4	ns

6.8 Operating Characteristics

 T_A = 25°C

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT
			TYP	TYP	TYP	TYP	
C _{pd}	Power dissipation capacitance	f = 10 MHz	18	18	19	22	pF

6.9 Typical Characteristics

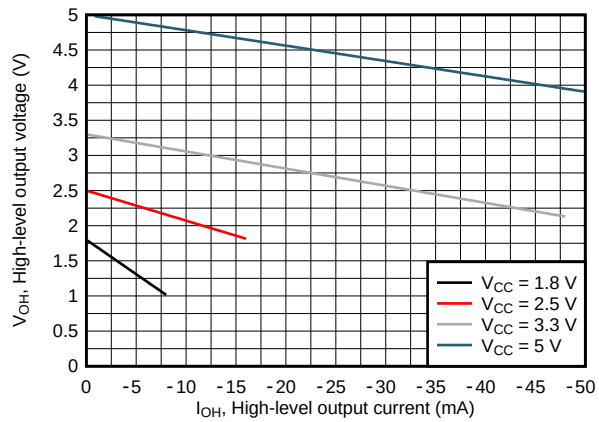


Figure 1. Simulated typical high-level output voltage (V_{OH}) across high-level output current (I_{OH}) at common supply values

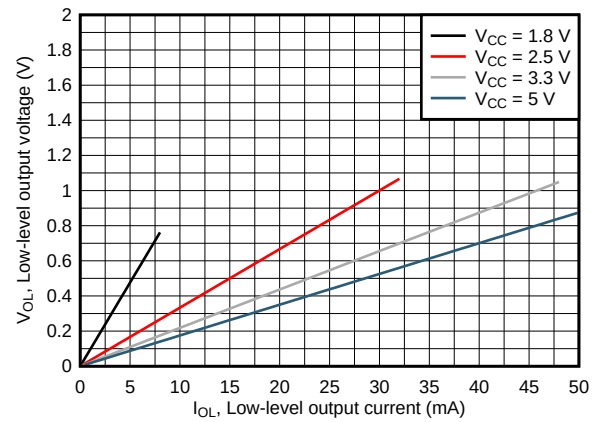
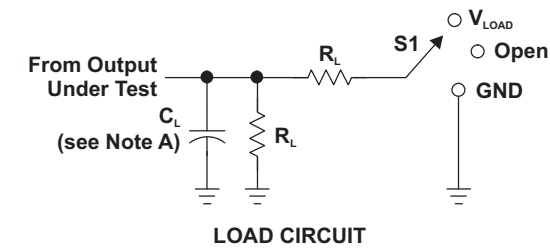


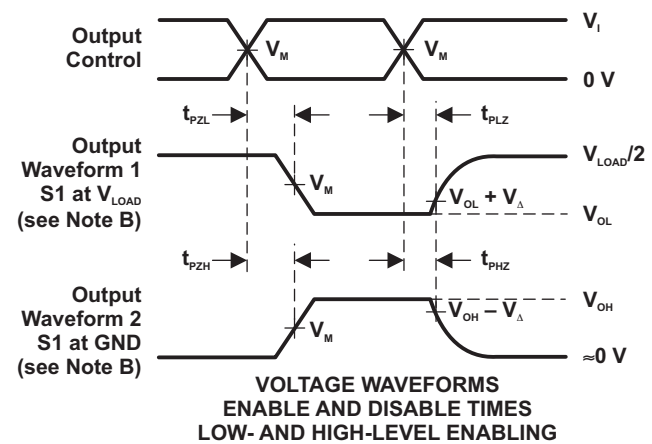
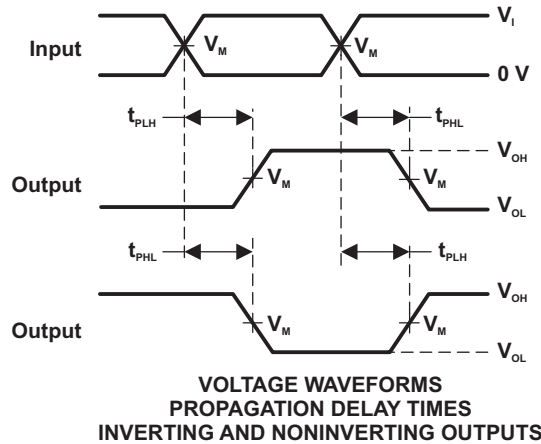
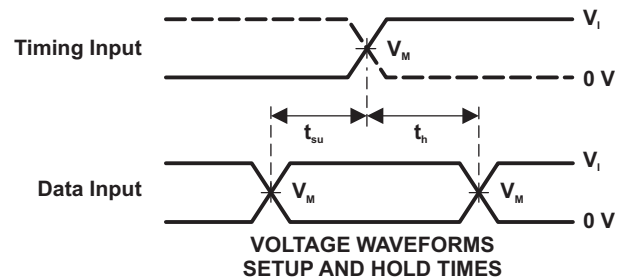
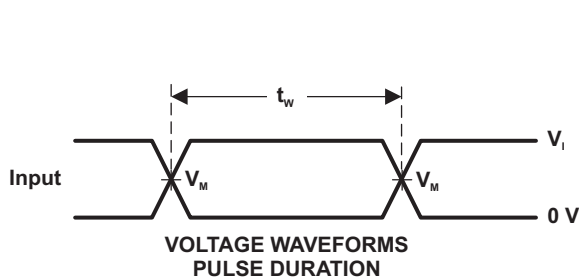
Figure 2. Simulated typical low-level output voltage (V_{OL}) across low-level output current (I_{OL}) at common supply values

7 Parameter Measurement Information



TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_o = 50\ \Omega$.
 - D. The outputs are measured one at a time, with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .
 - H. All parameters and waveforms are not applicable to all devices.

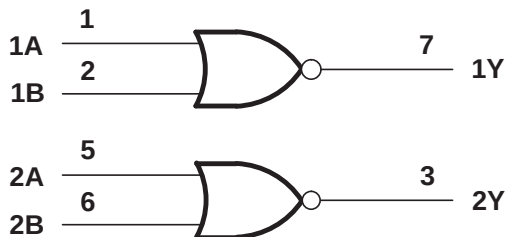
Figure 3. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74LVC2G02 device contains two 2-input positive-NOR gates and each gate performs the Boolean function $Y = A + B$ or $Y = \overline{A} \cdot \overline{B}$. This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

8.2 Functional Block Diagram



8.3 Feature Description

- Wide operating voltage range.
 - Operates from 1.65 V to 5.5 V.
- Allows down voltage translation.
- Inputs accept voltages to 5.5 V.
- I_{off} feature allows voltages on the inputs and outputs, when V_{CC} is 0 V.

8.4 Device Functional Modes

**Table 1. Function Table
(Each Gate)**

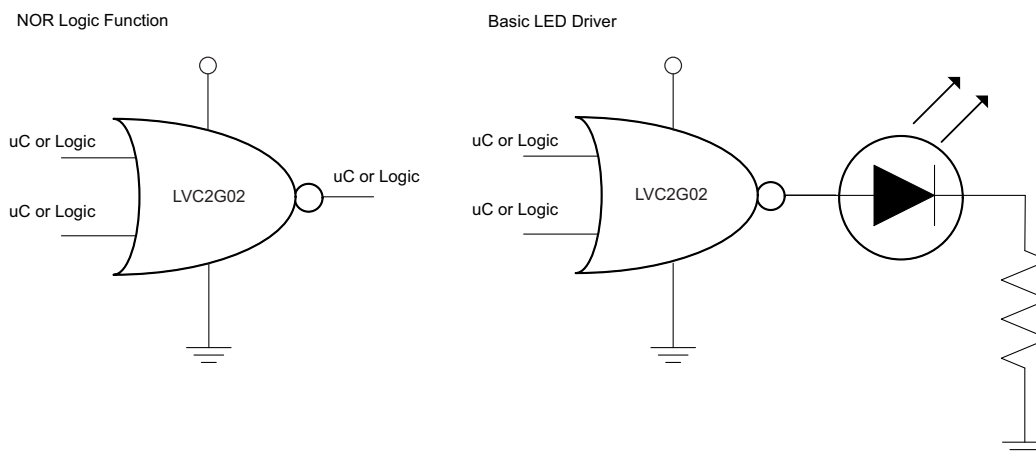
INPUTS		OUTPUT Y
A	B	
H	X	L
X	H	L
L	L	H

9 Application and Implementation

9.1 Application Information

The SN74LVC2G02 is a high-drive CMOS device that can be used for implement NOR logic with a high output drive, such as an LED application. It can produce 24-mA of drive current at 3.3 V making it Ideal for driving multiple outputs and good for high speed applications up to 100 Mhz. The inputs are 5.5-V tolerant allowing translation down to V_{CC} .

9.2 Typical Application



9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads, so routing and load conditions should be considered to prevent ringing.

9.2.2 Detailed Design Procedure

1. Recommended Input Conditions:

- Rise time and fall time specs. See ($\Delta t/\Delta V$) in the [Recommended Operating Conditions](#) table.
- Specified high and low levels. See (V_{IH} and V_{IL}) in the [Recommended Operating Conditions](#) table.
- Inputs are overvoltage tolerant allowing them to go as high as (V_I max) in the [Recommended Operating Conditions](#) table at any valid V_{CC} .

2. Recommend Output Conditions:

- Load currents should not exceed (I_O max) per output and should not exceed total current (continuous current through V_{CC} or GND) for the part. These limits are located in the [Absolute Maximum Ratings](#) table.
- Outputs should not be pulled above V_{CC} .

Typical Application (continued)

9.2.3 Application Curves

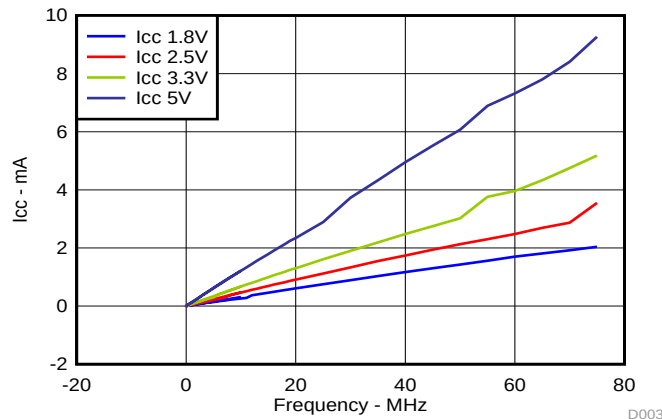


Figure 4. I_{CC} vs Frequency

10 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in the [Recommended Operating Conditions](#) table.

Each VCC pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1-μF capacitor is recommended. If there are multiple VCC pins, then a 0.01-μF or 0.022-μF capacitor is recommended for each power pin. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. A 0.1-μF and 1-μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

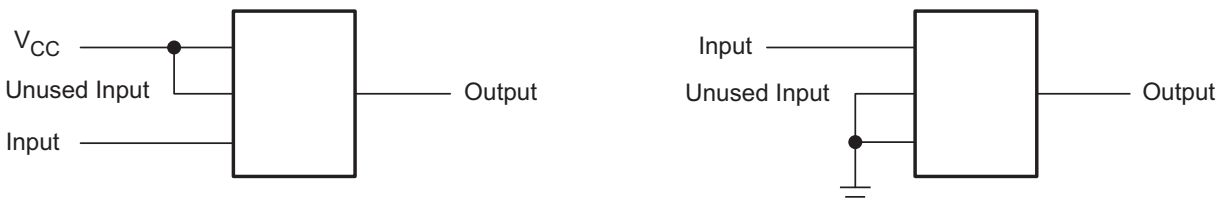
11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs should not ever float.

In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or VCC, whichever makes more sense or is more convenient.

11.2 Layout Example



12 器件和文档支持

12.1 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.2 商标

NanoFree, E2E are trademarks of Texas Instruments.

12.3 静电放电警告



ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

12.4 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC2G02DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C02 (R, Z)	Samples
SN74LVC2G02DCTRE4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C02 (R, Z)	Samples
SN74LVC2G02DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C02J, C02Q, C02R)	Samples
SN74LVC2G02DCUT	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C02J, C02Q, C02R)	Samples
SN74LVC2G02YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	CBN	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) **MSL, Peak Temp.** - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

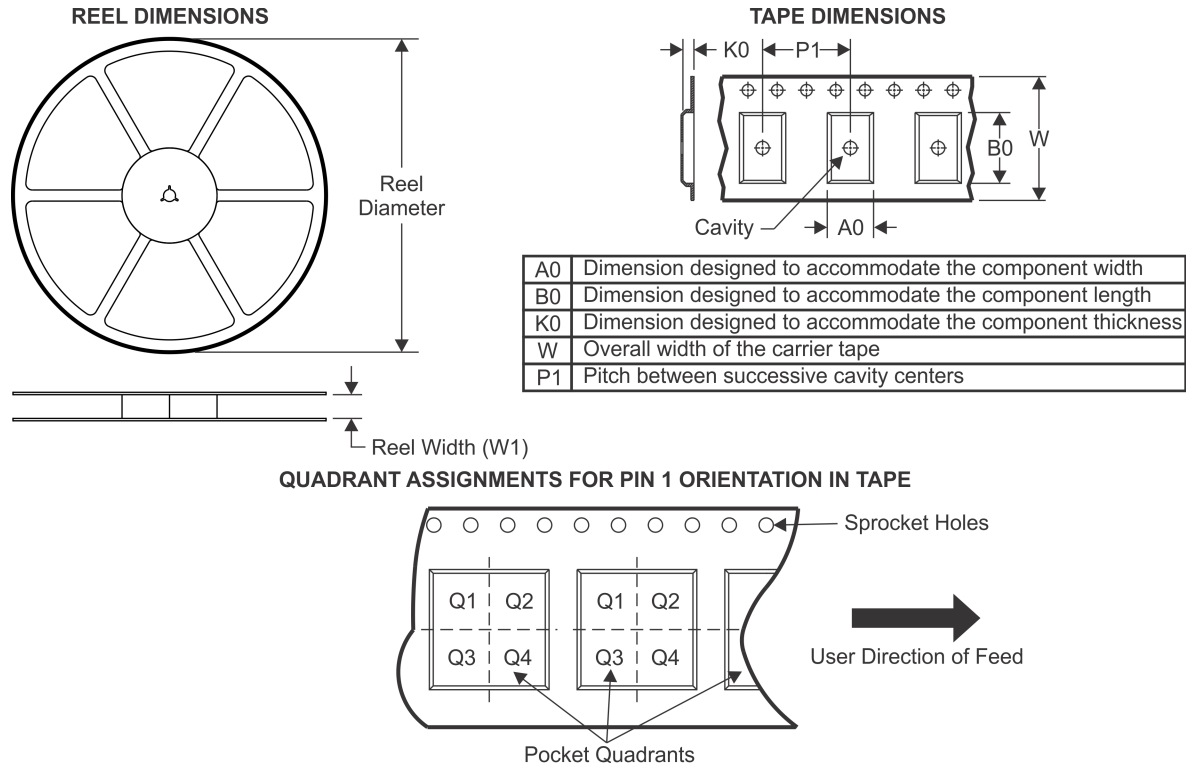
(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) **Lead finish/Ball material** - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

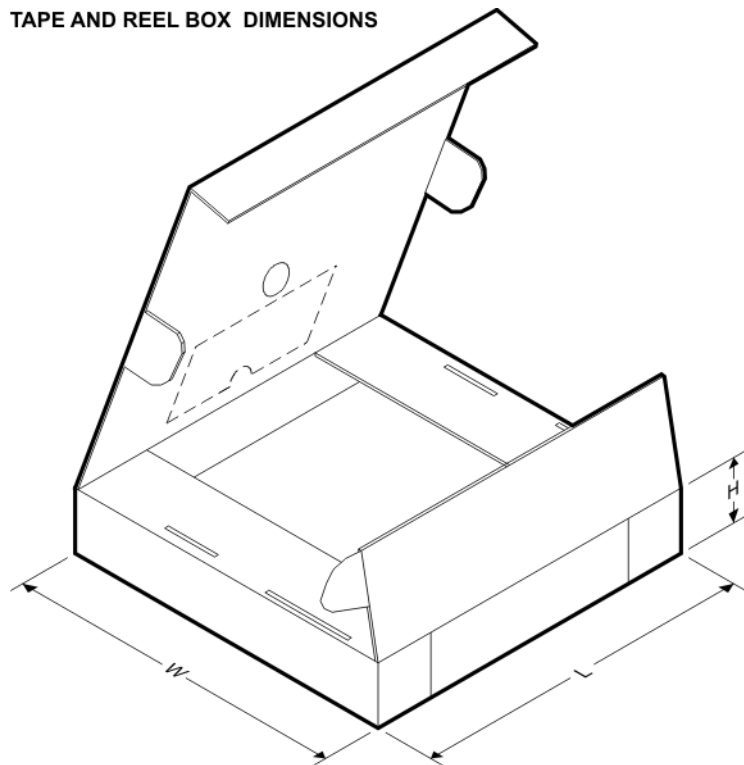
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2G02DCTR	SM8	DCT	8	3000	177.8	12.4	3.45	4.4	1.45	4.0	12.0	Q3
SN74LVC2G02DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G02DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G02DCUR	VSSOP	DCU	8	3000	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G02DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G02DCUT	VSSOP	DCU	8	250	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G02DCUT	VSSOP	DCU	8	250	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G02YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

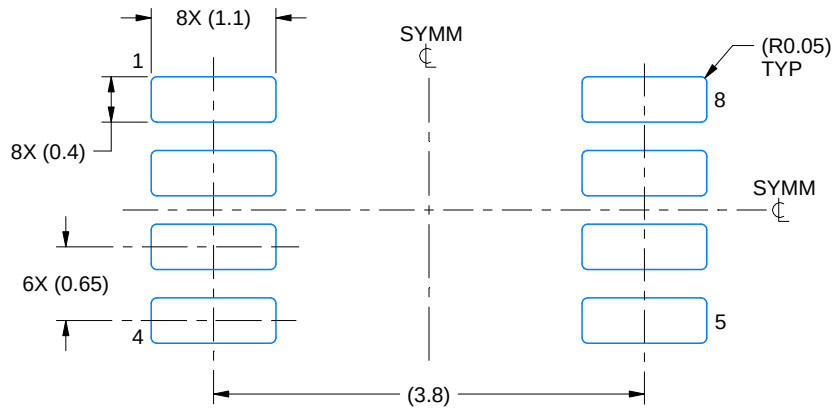
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2G02DCTR	SM8	DCT	8	3000	183.0	183.0	20.0
SN74LVC2G02DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G02DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G02DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G02DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
SN74LVC2G02DCUT	VSSOP	DCU	8	250	180.0	180.0	18.0
SN74LVC2G02DCUT	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G02YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0

EXAMPLE BOARD LAYOUT

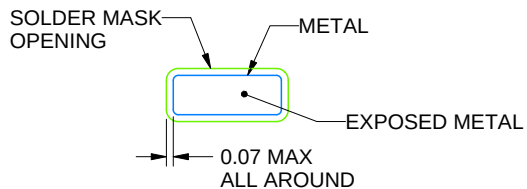
DCT0008A

SSOP - 1.3 mm max height

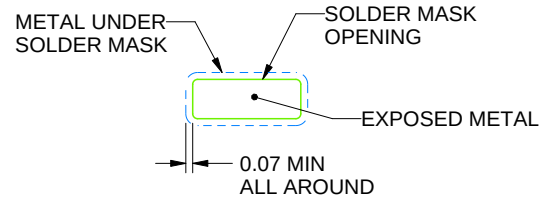
SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



NON SOLDER MASK
DEFINED



SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4220784/B 07/2020

NOTES: (continued)

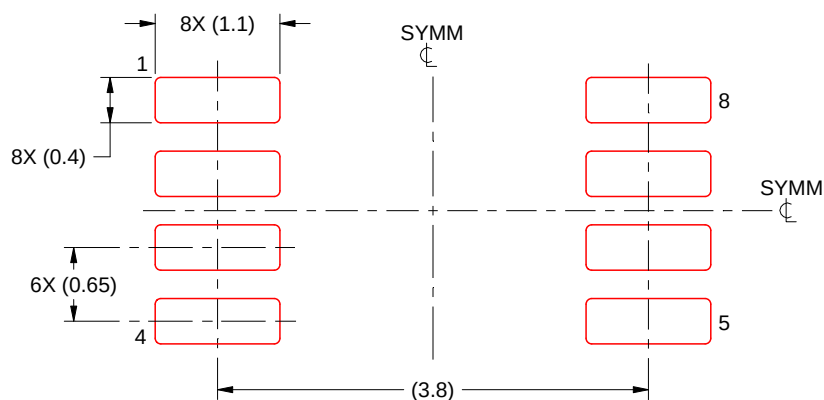
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DCT0008A

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



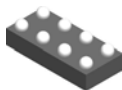
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4220784/B 07/2020

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

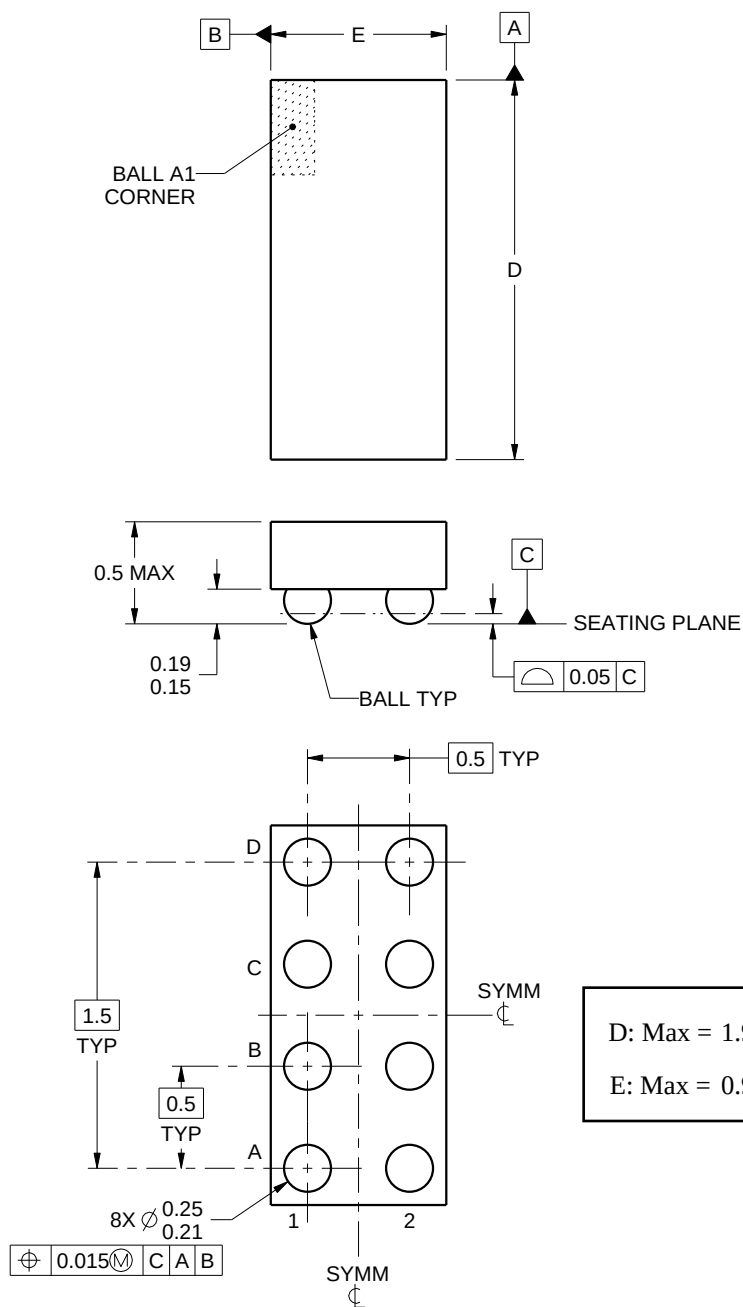
YZP0008



PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



4223082/A 07/2016

NOTES:

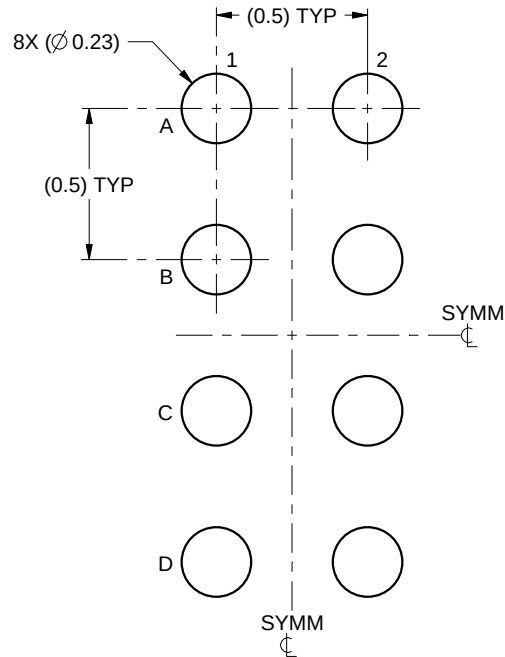
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

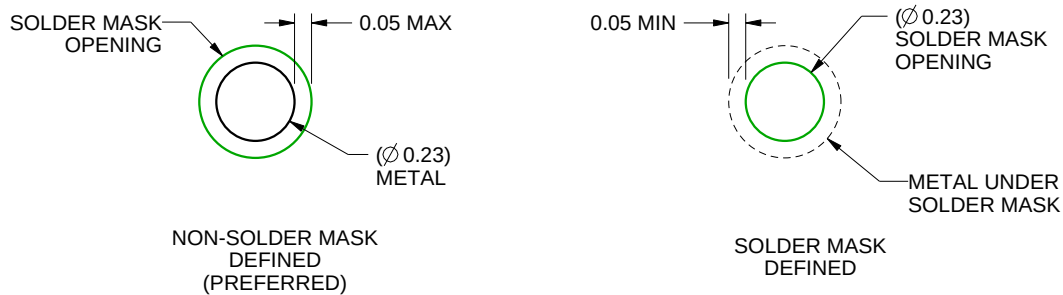
YZP0008

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE
SCALE:40X



SOLDER MASK DETAILS
NOT TO SCALE

4223082/A 07/2016

NOTES: (continued)

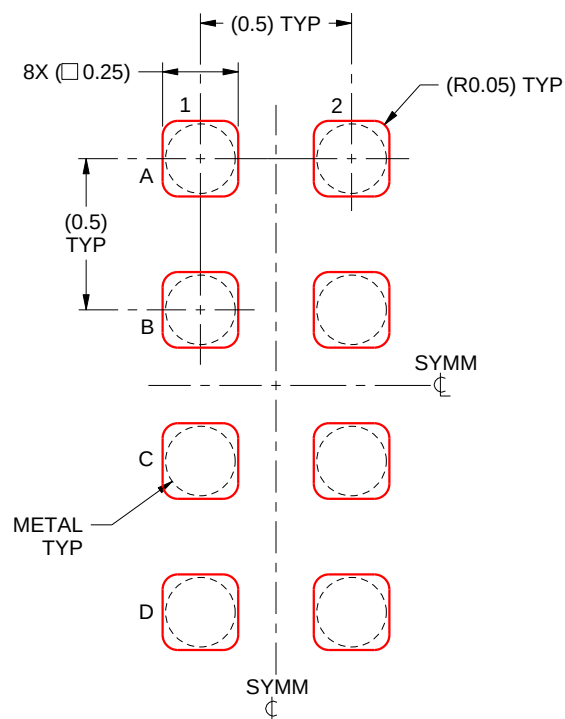
- Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).

EXAMPLE STENCIL DESIGN

YZP0008

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

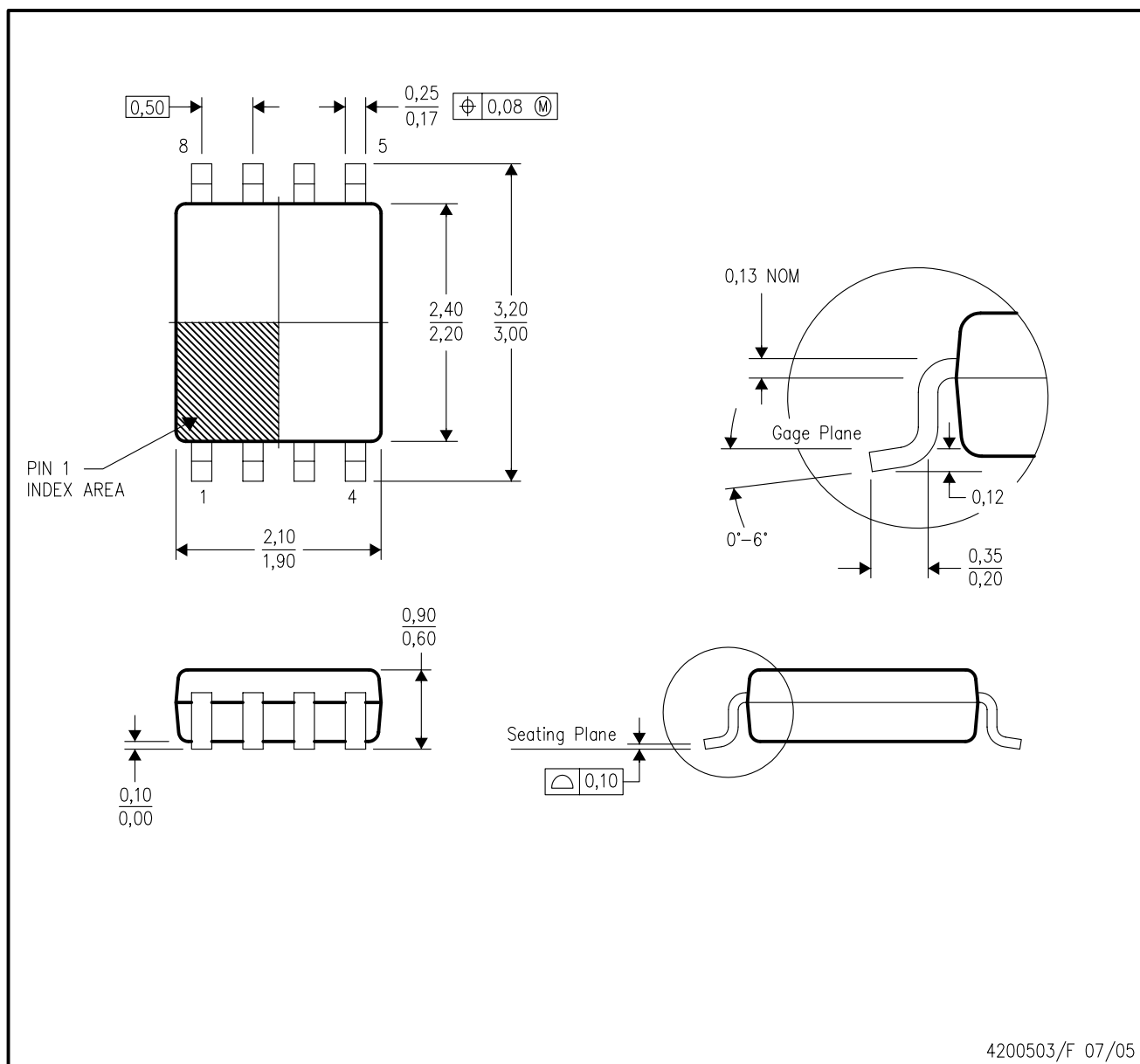
4223082/A 07/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)

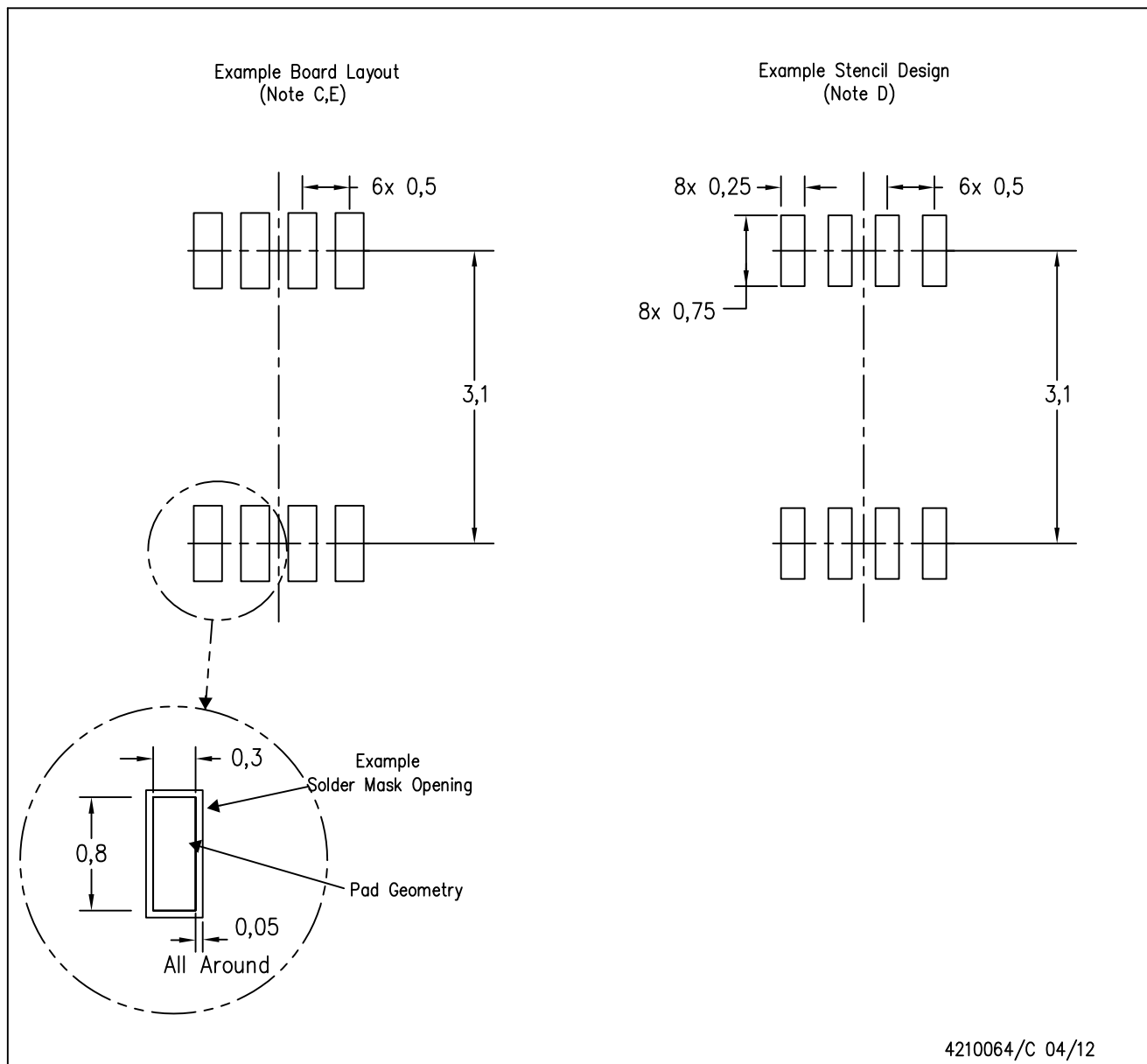


NOTES:

- All linear dimensions are in millimeters.
- This drawing is subject to change without notice.
- Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- Falls within JEDEC MO-187 variation CA.

DCU (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

重要声明和免责声明

TI 提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做任何明示或暗示的担保，包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他安全、安保或其他要求。这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的应用。严禁对这些资源进行其他复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，TI 对此概不负责。

TI 提供的产品受 TI 的销售条款 (<https://www.ti.com.cn/zh-cn/legal/termsofsale.html>) 或 [ti.com.cn](https://www.ti.com.cn) 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122
Copyright © 2021 德州仪器半导体技术（上海）有限公司